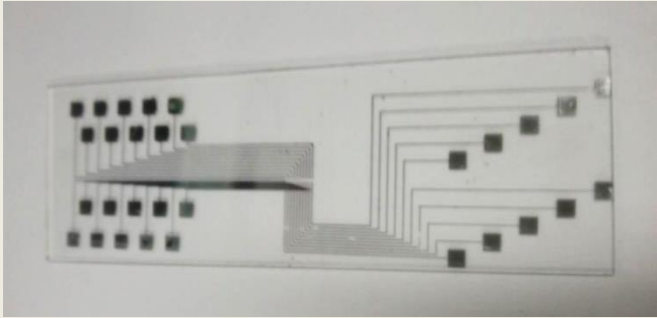


# Metal Lift-off Processes: (Glass + Pt) and (Si + Au-Pd)

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| Process                  | Pt on Glass  | Au-Pd on Si  |
|--------------------------|--|--|
| <b>Substrate</b>         | <b>Glass</b>   | <b>Si</b>  |
| <b>1. Clean</b>          | Acetone→IP alcohol→ DI water   | Acetone→IP alcohol→ DI water   |
| <b>2. Dry</b>            | N <sub>2</sub> gun→ hotplate: 200°C-5min   | N <sub>2</sub> gun→ hotplate: 200°C-5min   |
| <b>3. Spin-coat</b>      | Shipley 2000 rmp, 45s  | Shipley 2000 rmp, 45s  |
| <b>4. Prebake</b>        | 90°C-90s   | 90°C-90s   |
| <b>5. UV pattern</b>     | 6.06 mw/cm <sup>2</sup> , 40s  | 6.06 mw/cm <sup>2</sup> , 40s  |
| <b>6. Post bake</b>      | 90°C-90s   | 90°C-90s   |
| <b>7. Develop</b>        | AZ351:DI water (1:5), 1-3min ultrasonic bath (the time is different from sample to sample. Watch your sample every 30s to avoid losing feature). | AZ351:DI water (1:5), 1-3min ultrasonic bath (the time is different from sample to sample. Watch your sample every 30s to avoid losing feature). |
| <b>8. Rinse</b>          | DI water   | DI water   |
| <b>9. Dry</b>            | N <sub>2</sub> gun→ hotplate 70C-90s   | N <sub>2</sub> gun→ hotplate 70C-90s   |
| <b>10. UV pattern</b>    | 6.06 mw <sup>2</sup> /cm <sup>2</sup> , 40s (to weaken the photoresist)  | 6.06 mw <sup>2</sup> /cm <sup>2</sup> , 40s (to weaken the photoresist)  |
| <b>11. Metal Sputter</b> | <b>Titanium 5 nm + Pt 10 nm</b>  | <b>Au/Pd (Hummer VI):<br/>V = 8.5V, I = 10 mA, t = 10 min)</b>   |
| <b>12. Strip</b>         | 1165, 2min ultrasonic bath (watch the sample every 30s)  | 1165, 2 min ultrasonic bath (watch the sample every 30s)   |
| <b>13. Wash</b>          | Acetone→IP alcohol→ DI water   | Acetone→IP alcohol→ DI water   |
| <b>14. Dry</b>           | N <sub>2</sub> gun→ hotplate 70°C-90s  | N <sub>2</sub> gun→ hotplate 70°C-90s  |
| <b>15. Result</b>        | Clean features<br>   | Clean features   |

